

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	15952	(polish\$4 or grind\$4 or ground or CMP or chamfer\$4) and capacitor and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/24 11:08	
2	BRS	L2	6366	1 and ((trench or groove) same (Si or polysilicon or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/24 11:06	
3	BRS	L3	5895	2 and (etch\$4 or RIE or ??RIE)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/24 11:07	
4	BRS	L4	5874	(polish\$4 or grind\$4 or ground or CMP) and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/05/24 11:08	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	5623	4 and semiconductor\$4	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/05/24 11:08	
6	BRS	L6	348	((polish\$4 or grind\$4 or ground or CMP) near10 selective\$4) and 3	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/05/24 11:08	
8	BRS	L8	338	6 and semiconductor\$4	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/05/24 11:09	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	5826	selective\$6 near10 (polish\$4 or grind\$4 or CMP)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB-	2004/05/2 4 07:17	
2	BRS	L2	258	1 same (bevel\$4 or peripher\$6)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB-	2004/05/2 4 07:17	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
26	BRS	L26	12844	(polish\$4 or grind\$4 or CMP or ground) and chamfer\$6	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/05/2 4 10:47	
27	BRS	L27	272	26 and (trench or groove) and capacitor	USPA T; US-P GPUB	2004/05/2 4 10:47	
28	BRS	L28	191	27 and @ad<=20000530	USPA T; US-P GPUB	2004/05/2 4 10:47	
29	BRS	L29	118	27 and @rlad<=20000530	USPA T; US-P GPUB	2004/05/2 4 10:48	
30	BRS	L30	231	28 or 29	USPA T; US-P GPUB	2004/05/2 4 10:48	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	18641	(polish\$4 or grind\$4 or CMP) near20 (bevel\$4 or peripher\$6)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/2 4 08:11	
17	BRS	L17	4918	16 and (semiconductor or (integrated adj circuit) or capacitor or Si or silicon or polysilicon)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/2 4 10:25	
19	BRS	L19	3395	16 and (semiconductor or (integrated adj circuit) or capacitor or Si or silicon or polysilicon)	USPA T; US-P GPUB	2004/05/2 4 10:25	
20	BRS	L20	225	19 and (trench or groove) and capacitor	USPA T; US-P GPUB	2004/05/2 4 10:26	
21	BRS	L21	113	20 and @ad<=20000530	USPA T; US-P GPUB	2004/05/2 4 10:26	
22	BRS	L22	74	20 and @rlad<=20000530	USPA T; US-P GPUB	2004/05/2 4 10:26	
23	BRS	L23	153	21 or 22	USPA T; US-P GPUB	2004/05/2 4 10:26	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	5826	selective\$6 near10 (polish\$4 or grind\$4 or CMP)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/2 4 08:10	
2	BRS	L2	258	1 same (bevel\$4 or peripher\$6)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2004/05/2 4 08:03	
3	BRS	L3	44	1 same (bevel\$4 or peripher\$6)	EPO; JPO; DERW ENT; IBM_ TDB	2004/05/2 4 07:18	
4	BRS	L4	214	1 same (bevel\$4 or peripher\$6)	USPA T; US-P GPUB	2004/05/2 4 07:29	
5	BRS	L5	157	4 and @ad<=20000530	USPA T; US-P GPUB	2004/05/2 4 08:04	
6	BRS	L6	47	4 and @rlad<=20000530	USPA T; US-P GPUB	2004/05/2 4 07:30	
7	BRS	L7	165	5 or 6	USPA T; US-P GPUB	2004/05/2 4 07:30	
8	BRS	L8	33	7 and bevel\$6	USPA T; US-P GPUB	2004/05/2 4 07:33	
9	BRS	L9	132	7 not 8	USPA T; US-P GPUB	2004/05/2 4 07:33	